

# 350V N-Channel Enhancement Mode MOSFET

## **General Features**

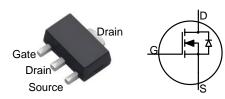
- Proprietary Advanced Planar Technology
- Rugged Polysilicon Gate Cell Structure
- Fast Switching Speed
- RoHS Compliant
- ➤ Halogen-free available

Ap	pli	cati	ons

- ➤ High Efficiency SMPS
- ➤ Adaptor/Charger
- > Active PFC

$BV_{DSS}$	R <sub>DS(ON)</sub> (Max.)	$I_D$
350V	15 Ω	200mA

#### **SOT-89**



# **Ordering Information**

	Part Number Package FTX15N35G SOT-89		Marking	Remark
			N35	Halogen Free

# **Absolute Maximum Ratings**

T<sub>A</sub>=25°C unless otherwise specified

Symbol	Parameter	FTX15N35G	Unit
$V_{\mathrm{DSS}}$	Drain-to-Source Voltage <sup>[1]</sup>	350	V
$I_{\mathrm{D}}$	Continuous Drain Current	0.2	Δ.
$I_{DM}$	Pulsed Drain Current <sup>[2]</sup>	0.6	A
$P_{D}$	Power Dissipation	1.0	W
$V_{GS}$	Gate-to-Source Voltage	±20	V
$T_{ m L}$	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300	°C
T <sub>J</sub> and T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

# **Thermal Characteristics**

Symbol	Parameter	FTX15N35G	Unit
$R_{ heta JA}$	Thermal Resistance, Junction-to-Ambient	125	K/W



## **Electrical Characteristics**

#### **OFF** Characteristics

T<sub>A</sub> =25°C unless otherwise specified

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
$BV_{DSS}$	Drain-to-Source Breakdown Voltage	350			V	$V_{GS}$ =0V, $I_{D}$ =250 $\mu$ A
$\triangle BV_{DSS}/\triangle T_{J}$	Breakdown Voltage Temperature Coefficient		0.35		V/°C	Reference to 25°C, $I_D$ =250 $\mu$ A
				1	μΑ	$V_{DS}=350V$ , $V_{GS}=0V$
$I_{DSS}$	Drain-to-Source Leakage Current			100	μΑ	$V_{DS}=350V$ , $V_{GS}=0V$ $T_{J}=125$ °C
$I_{GSS}$	Gate-to-Source Leakage Current			20		$V_{GS} = +20V, V_{DS} = 0V$
				-20	μA	$V_{GS}$ =-20V, $V_{DS}$ =0V

## **ON Characteristics**

## T<sub>A</sub> =25°C unless otherwise specified

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
R <sub>DS(ON)</sub>	Static Drain-to-Source On-Resistance		8	15	Ω	$V_{GS}=10V$ , $I_{D}=200mA^{[3]}$
$V_{\text{GS(TH)}}$	Gate Threshold Voltage	1		3	V	$V_{GD} = 0V, I_D = 250 \mu\text{A}$

#### **Dynamic Characteristics**

#### Essentially independent of operating temperature

Symbol	Parameter	Min.	Тур.	Max.	Unit	<b>Test Conditions</b>
$C_{ISS}$	Input Capacitance		32.58			V <sub>GS</sub> =0V
Coss	Oput Capacitance		5.36		pF	$V_{DS}=25V$
$C_{RSS}$	Reverse Transfer Capacitance		0.75			$f=1.0MH_Z$
$t_{d(ON)}$	Turn-on Delay Time		14			$V_{DD} = 25V, I_D=80mA$ $R_G = 25Ohm$ $V_{GS} = 10V\sim0V$
$t_{rise}$	Rise Time		10		ne	
t <sub>d(OFF)</sub>	Turn-off Delay Time		24		ns	
$t_{\mathrm{fall}}$	Fall Time		36			

#### **Source-Drain Diode Characteristics**

#### T<sub>A</sub>=25°C unless otherwise specified

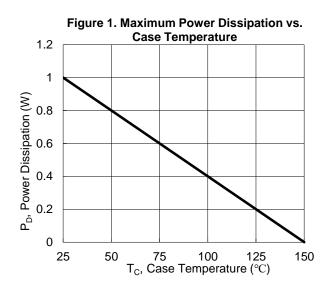
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Symbol	Parameter	Min	Тур.	Max.	Units	<b>Test Conditions</b>
$V_{\mathrm{SD}}$	Diode Forward Voltage			1.8	V	$I_{SD} = 200 \text{ mA}, V_{GS} = 0 \text{ V}$

### NOTE:

- [1]  $T_J = +25$ °C to +150°C
- [2] Repetitive rating, pulse width limited by maximum junction temperature.
- [3] Pulse width \( 380 \mu s; \) duty cycle \( 2\% \).



# **Typical Characteristics**



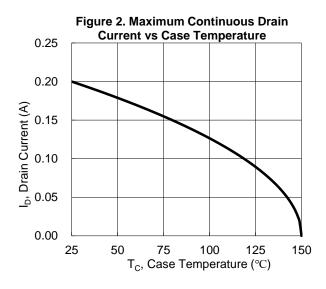
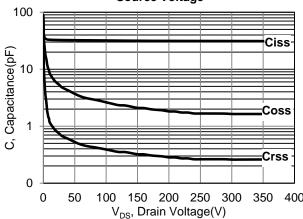


Figure 3. Typical Capacitance vs. Drain-to-Source Voltage



# **Switching Waveforms and Test Circuit**

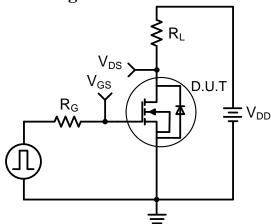


Figure 4. Resistive Switching Test Circuit

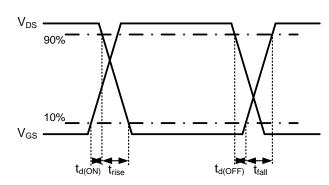
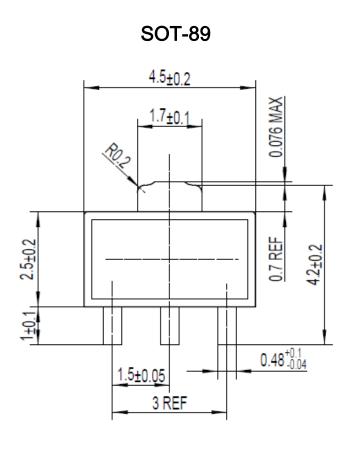
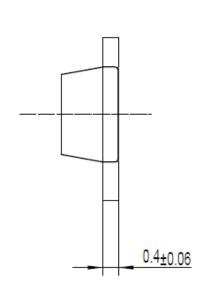


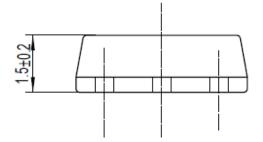
Figure 5. Resistive Switching Waveforms



# **Package Dimensions**









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ADD: 4F, D26, UESTC National Science Park No. 1 Shuangxing Avenue, Gongxing Street,

Shuangliu District, Chengdu, China (Sichuan) Pilot Free Trade Zone.

Tel: +86-28-8523-2215 Email: sales@ark-micro.com http://www.ark-micro.com

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